



University of Tehran
School of Electrical and Computer Engineering

Course:	Quantum Transport		
Course type:	Elective	EE	Credit: 3
Level:	Graduate		
Co-requisite(s):			
Prerequisite(s):	Quantum Mechanics		
Prerequisite by topic:	Being familiar with the concepts of quantum mechanics and the principles of semiconductors		
Textbook(s):	<p>[1] S. Datta, “<i>Quantum Transport: From Atoms to Transistors</i>,” Cambridge University Press; (2005).</p> <p>[2] S. Datta, “<i>Electronic Transport in Mesoscopic Systems</i>,” Cambridge University Press; (1995).</p> <p>[3] S. Datta, “<i>Quantum Phenomena</i>,” (Modular Series on Solid State Devices, Vol 8), Addison-Wesley (1989).</p>		
Coordinator:	Mahdi Pourfath		
Goals:	<p>Introducing the students with the following topics:</p> <ul style="list-style-type: none"> – Quantum effects in nanoelectronic devices – Modeling nanoelectronic devices – Including contacts and scattering mechanisms – Advanced numerical techniques for the analysis of nanoelectronic devices 		
Outcome:	<p>Upon successful completion of the course, students will be able to:</p> <ul style="list-style-type: none"> – Deeply understand the principles of nanoelectronic devices – Model nanoelectronic devices – Apply advanced numerical techniques to analyze and perform optimization studies of nanoelectronic devices 		
Topics:	<p>Review of Modern Physics: Particle-wave like nature of electrons, Schroedinger equation, uncertainty principles, quantum many-body systems</p> <p>Basis Functions and Band-Structure: Electrons in periodic potential, Basis functions, Atomic orbitals as the basis function, tight-binding model, spin-orbit interaction and its effect on the electronic band structure, multi-orbital bandstructure model</p>		

	<p>The Effect of Electron-Electron Interaction on the Electronic Bandstructure: Density functional theory (DFT), exchange and correlation potential, LDA and GGA, parameters for ab-initio simulations</p> <p>Subbands: Quantum dots, nanowires, quantum wells, contact resistance, the resistance associated with scatters, velocity of a subband, density of states in 0D, 1D, 2D, and 3D</p> <p>Level Broadening: Open systems, uncertainty in energy and time, finite life time due to scattering and interaction with contacts, local density of states, modeling contacts</p> <p>Coherent Transport: Density matrix, Green's functions, inflow, outflow, transmission, spectral functions</p> <p>Incoherent Transport: Modeling scattering using self-energies, lattice vibrations and phonons, electron-phonon interaction, electron- photon interaction, self-consistent Born approximation</p> <p>Device Simulation: Numerical techniques and the flowcharts of evaluating the Green's functions for the analysis of nanoelectronic devices, Analysis of nanoscale device from macroscopic to atomistic scale</p>								
Grading:	<table data-bbox="511 798 941 934"> <tr> <td>Assignments:</td> <td>5%</td> </tr> <tr> <td>Projects:</td> <td>15%</td> </tr> <tr> <td>Midterm exams:</td> <td>40%</td> </tr> <tr> <td>Final exam:</td> <td>40%</td> </tr> </table>	Assignments:	5%	Projects:	15%	Midterm exams:	40%	Final exam:	40%
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Further readings:									
Prepared by:	Mahdi Pourfath								
Date:	Nov. 2017								